



2SK2618LS

N- Channel MOS Silicon FET
Very High-Speed Switching Applications

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Low Qg

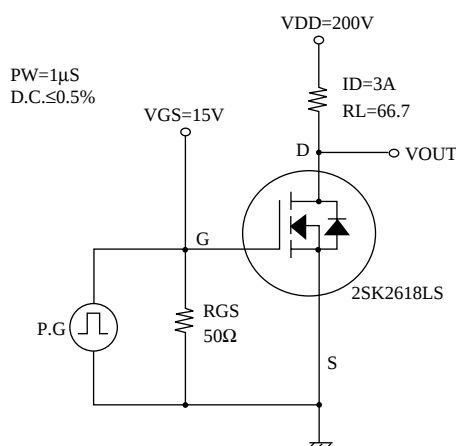
Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	V _{DSS}	500	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current (DC)	I _D	5	A
Drain Current (Pulse)	I _{DP}	20	A
Allowable power Dissipation	P _D (T _c =25°C)	30	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

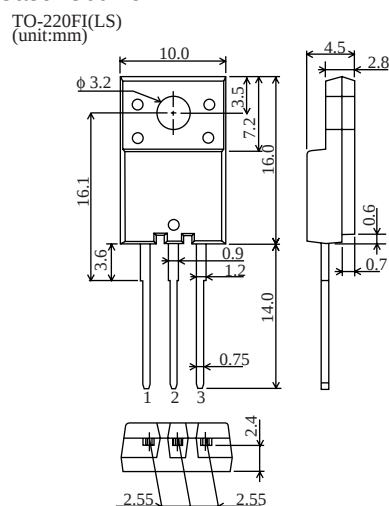
Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR) _{DSS}	I _D =1mA , V _{GS} =0	500			V
Zero Gate Voltage Drain Current	I _{DSS}	V _D =500V , V _{GS} =0			1.0	mA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±30V , V _D =0			±100	nA
Cutoff Voltage	V _{GS(off)}	V _D =10V , I _D =1mA	3.5		5.5	V
Forward Transfer Admittance	y _{fs}	V _D =10V , I _D =3A	1.5	3.0		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D =3A , V _{GS} =15V		0.95	1.25	Ω
Input Capacitance	C _{iss}	V _D =20V , f=1MHz		700		pF
Output Capacitance	C _{oss}	V _D =20V , f=1MHz		250		pF
Reverse Transfer Capacitance	C _{rss}	V _D =20V , f=1MHz		120		pF
Total Gate Charge	Q _g	V _D =200V , I _D =5A V _{GS} =10V		20		nC
Turn-ON Delay Time	t _{d(on)}	See Specified Test Circuit		20		ns
Rise Time	t _r			20		ns
Turn-oFF Delay Time	t _{d(off)}			50		ns
Fall Time	t _f			25		ns
Diode Forward Voltage	V _{SD}	I _S =5A , V _{GS} =0			1.2	V

Switching Time Test Circuit



Case Outline



Specifications and information herein are subject to change without notice.

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